



		ATTY. DOCKET NO.:	APPLICATION NO.:
		4717-13300	10/809,918
		APPLICANT:	
		C. Maleville et al.	
		FILING DATE:	GROUP:
		March 26, 2004	2812 2824

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
BEO	AA	4,743,767	5/1988	Plumb et al.	250	492.2	
BEO	AB	4,751,393	6/1988	Corey, Jr. et al.	250	492.21	
BEO	AC	4,807,994	2/1989	Felch et al.	356	326	
BEO	AD	5,374,564	12/1994	Bruel	437	24	
	AE	5,834,463	11/1998	Ohkawa et al.	514	220	
BEO	AF	5,998,798	12/1999	Halling et al.	250	492.21	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AG							
	AH							
	AI							

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

BEO	AJ	Scott M. Baumann, "Rutherford Backscattering Spectrometry (RBS), Charles Evans & Associates, Specialists in Materials Characterization, pp. 1-15.
	AK	
	AL	
	AM	
	AN	
	AO	

EXAMINER	DATE CONSIDERED
<i>Becky E. Owens</i>	<i>9.13.04</i>

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

			ATTY DOCKET NO 4717-1330U	APPLICATION NO 10/809,918
APPLICANT C. Maleville et al.				
FILING DATE March 26, 2004			GROUP 2812	

## U.S. PATENT DOCUMENTS

EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAMES	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
BEO	AA	760 409	6/1998	Chen et al.	250	492.21	
	AB	BEO 9.17.04					
	AC						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							VRS NO
BEO	AD	JP 61 043417 A English Abstract	3/1986	Japan 250			X
BEO	AE	WO 99 08307 A	2/1999	PCT			X
	AF						

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc)

BEO	AG	Shuetekatte et al., XP004195210, "Dose and implantation temperature influence extended defects nucleon in c-Si", Nuclear instruments and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing Company, Vol. 164-165, pp. 425-430 (2000)
BEO	AH	L.J. Huang et al., XP000905645, "Model for blistering of hydrogen implanted silicon and its application to silicon-on-quartz", Electrochemical Society Proceedings, Processing of 8th International Symposium on Semiconductor Silicon Vol 98-1, pp. 1373-1384 (1998)
	AJ	Da Silva et al., XP004242656, "The effects of implantation temperature on He bubble formation in silicon", Nuclear instrument and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing' Company, Amsterdam, NL, Vol. 175-177, pp. 335-339 (2001)
BEO	AJ	Bruel et al., XP000611125, "Application of Hydrogen Ion Beams To Silicon on Insulator Material Technology", Nuclear instrument and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing' Company, Amsterdam, NL, Vol. 108, No. 3, pp. 313-319 (1996)
BEO	AK	Lanzieri et al., XP000073904 "Activation Uniformity Improvement of Undoped semi-insulating Gaas with an improved Post-Implant Anneal Furnace", Journal of applied Physics, New York, Vol. 66, No. 8, pp 3643-3644 (1989)  BEO 9.17.04

EXAMINER	DATE CONSIDERED
Beth E. Owens	9.17.04